

BSTMFNP8G08AWP

I. Product Introduction

1.1. Product Overview

BSTMFNP8G08AWP For capacity 1G×8bit Non-volatility SLC NAND FLASH storage Device
Support ONFI 1.0 The device is divided into blocks that can be erased independently, so
The device contains 4096 blocks, by 64 pages, each consisting of 32A series of NAND
Distructure Flash. The programming operation writes 4352 Typical time per byte/page
for 200us, Erase 256K Typical times for bytes/blocks are 2ms The data read cycle in a page
is 25ns.

1.2. Product Features

- Supply voltage VCC: 2.7V~3.6V
- Synchronous (4096+256) Byte Page Read
- Random read access maximum 35us
- Serial page read access is fastest 25ns
- Typical Page Programming Time 200us
- Block size: 256K+16K) byte
- Fast Block Erase Typical Value 2ms
- Supports fast data copying without external buffering
- Array layout: 4K+256) byte x 64 Page x 4096 piece
- Support ONFI 1.0 Parameter Table
- Operating temperature range: -55°C~125°C
- Erasing times: 3 Ten thousand times
- Data retention time: 10 Year
- Packaging type: plastic package TSOP48
- -External ECC need: 8Bit/512byte ECC

1.3. Corresponding to the situation of replacing foreign products

BSTMFNP8G08AWP Circuit and MICRON Company MT29F8G08ABACAWP Product compatibility,

It can replace imported devices in situation.